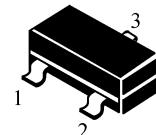


## NPN Switching Transistor

SOT-23

1. BASE
2. Emitter
3. Collector



### ■MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current-Continuous	I <sub>c</sub>	200	mAdc

### ■THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board(1) Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Total Device Dissipation Alumina Substrate, Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	417	°C/W
Solder Temperature/Solder Time	T/t	260/10	°C/S
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	150°C, -55 to +150°C	

## ■ ELECTRICAL CHARACTERISTICS

( $T_A=25^\circ\text{C}$  unless otherwise noted)

## ■ OFF CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage(3) ( $I_c=1.0\text{mA}_{\text{dc}}, I_B=0$ )	$V_{(\text{BR})\text{CEO}}$	40	—	Vdc
Collector-Base Breakdown Voltage ( $I_c=10\ \mu\text{A}_{\text{dc}}, I_E=0$ )	$V_{(\text{BR})\text{CBO}}$	60	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E=10\ \mu\text{A}_{\text{dc}}, I_c=0$ )	$V_{(\text{BR})\text{EBO}}$	6.0	—	Vdc
Base Cutoff Current ( $V_{\text{CE}}=30\text{Vdc}, V_{\text{EB}}=3.0\text{Vdc}$ )	$I_{\text{BEX}}$	—	50	nAdc
Collector Cutoff Current ( $V_{\text{CE}}=30\text{Vdc}, V_{\text{EB}}=3.0\text{Vdc}$ )	$I_{\text{CEX}}$	—	50	nAdc

## ■ ON CHARCTERISTICS(2)

Characteristic	Symbol	Min	Max	Unit
DC Current Gain ( $I_c=0.1\text{mA}_{\text{dc}}, V_{\text{CE}}=1.0\text{Vdc}$ )	$h_{\text{PE}}$			—
( $I_c=1.0\text{mA}_{\text{dc}}, V_{\text{CE}}=1.0\text{Vdc}$ )		40	—	
( $I_c=10\text{mA}_{\text{dc}}, V_{\text{CE}}=1.0\text{Vdc}$ )		70	—	
( $I_c=50\text{mA}_{\text{dc}}, V_{\text{CE}}=1.0\text{Vdc}$ )		100	300	
( $I_c=100\text{mA}_{\text{dc}}, V_{\text{CE}}=1.0\text{Vdc}$ )		60	—	
( $I_c=100\text{mA}_{\text{dc}}, V_{\text{CE}}=1.0\text{Vdc}$ )		30	—	
Collector-Emitter Saturation Voltage ( $I_c=10\text{mA}_{\text{dc}}, I_B=1.0\text{mA}_{\text{dc}}$ ) ( $I_c=50\text{mA}_{\text{dc}}, I_B=5.0\text{mA}_{\text{dc}}$ )	$V_{\text{CE}}(\text{sat})$	— —	0.25 0.4	Vdc
Base-Emitter Saturation Voltage ( $I_c=10\text{mA}_{\text{dc}}, I_B=1.0\text{mA}_{\text{dc}}$ ) ( $I_c=50\text{mA}_{\text{dc}}, I_B=5.0\text{mA}_{\text{dc}}$ )	$V_{\text{BE}}(\text{sat})$	0.65 —	0.85 0.95	Vdc

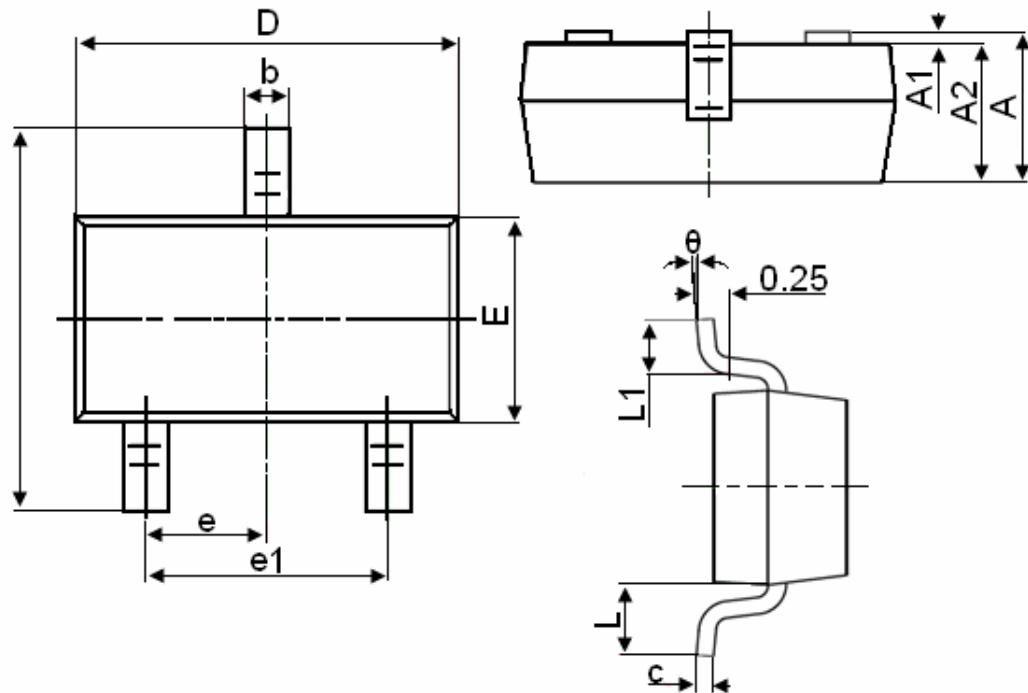
## ■ SMALL-SIGNAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Current-Gain-Bandwidth Product ( $I_c=10\text{mA}$ , $V_{CE}=-20\text{Vdc}$ , $f=100\text{MHz}$ )	$f_T$	300	—	MHz
Output Capacitance ( $V_{CB}=5.0\text{Vdc}$ , $I_E=0$ , $f=1.0\text{MHz}$ )	$C_{obo}$	—	4.0	pF
Input Capacitance ( $V_{EB}=0.5\text{Vdc}$ , $I_C=0$ , $f=1.0\text{MHz}$ )	$C_{ibo}$	—	8.0	pF
Input Impedance ( $V_{CE}=10\text{Vdc}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{KHz}$ )	$h_{ie}$	1.0	10	kΩ
Voltage Feedback Ratio ( $V_{CE}=10\text{Vdc}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{KHz}$ )	$h_{re}$	0.5	8.0	$\times 10^{-4}$
Small-Signal Current Gain ( $V_{CE}=10\text{Vdc}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{KHz}$ )	$h_{fe}$	100	400	—
Output Admittance ( $V_{CE}=10\text{Vdc}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{KHz}$ )	$h_{oe}$	1.0	40	μ mhos
Noise Figure ( $V_{CE}=5.0\text{Vdc}$ , $I_C=100 \mu \text{A}$ , $R_s=1.0 \text{ k}\Omega$ , $f=1.0\text{KHz}$ )	NF	—	5.0	dB

## ■ SWITCHING CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Delay Time	$t_d$	—	35	ns
Rise Time	$t_r$	—	35	
Storage Time	$t_s$	—	225	ns
Fall Time	$t_f$	—	75	

- FR-5=1.0×0.75×0.062in.
- Alumina=0.4×0.3×0.024in. 99.5%alumina.
- Pulse Width≤300us; Duty Cycle≤2.0%.
- Pulse Test: Pulse Width≤300us; Duty Cycle≤2.0%.

**SOT-23 Package Information**

Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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